

CMRDM3575

**SURFACE MOUNT  
N-CHANNEL AND P-CHANNEL  
ENHANCEMENT-MODE  
COMPLEMENTARY SILICON MOSFETS**

ATTOmini™



SOT-963 CASE

• Device is **Halogen Free** by design

**APPLICATIONS:**

- Load/Power switches
- Power supply converter circuits
- Battery powered portable devices

**MAXIMUM RATINGS:** (T<sub>A</sub>=25°C)

Drain-Source Voltage	
Gate-Source Voltage	
Continuous Drain Current (Steady State)	
Continuous Drain Current, t <sub>p</sub> ≤5.0s	
Power Dissipation	
Operating and Storage Junction Temperature	
Thermal Resistance	

**ELECTRICAL CHARACTERISTICS:** (T<sub>A</sub>=25°C)

SYMBOL	TEST CONDITIONS	N-CH (Q1)			P-CH (Q2)			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
I <sub>GSSF</sub> , I <sub>GSSR</sub>	V <sub>GS</sub> =5.0V, V <sub>DS</sub> =0	-	-	100	-	-	100	nA
I <sub>DSS</sub>	V <sub>DS</sub> =5.0V, V <sub>GS</sub> =0	-	-	50	-	-	50	nA
I <sub>DSS</sub>	V <sub>DS</sub> =16V, V <sub>GS</sub> =0	-	-	100	-	-	100	nA
BV <sub>DSS</sub>	V <sub>GS</sub> =0, I <sub>D</sub> =250μA	20	-	-	20	-	-	V
V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.4	-	1.0	0.4	-	1.0	V
r <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =100mA	-	1.5	3.0	-	4.0	5.0	Ω
r <sub>DS(ON)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =50mA	-	2.0	4.0	-	5.5	7.0	Ω
r <sub>DS(ON)</sub>	V <sub>GS</sub> =1.8V, I <sub>D</sub> =20mA	-	3.0	6.0	-	8.0	10	Ω
r <sub>DS(ON)</sub>	V <sub>GS</sub> =1.5V, I <sub>D</sub> =10mA	-	4.0	10	-	11	17	Ω
r <sub>DS(ON)</sub>	V <sub>GS</sub> =1.2V, I <sub>D</sub> =1.0mA	-	7.0	-	-	20	-	Ω
g <sub>FS</sub>	V <sub>DS</sub> =5.0V, I <sub>D</sub> =125mA	-	1.3	-	-	0.14	-	S
C <sub>rss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0, f=1.0MHz	-	2.2	-	-	4.0	-	pF
C <sub>iSS</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0, f=1.0MHz	-	9.0	-	-	10	-	pF
C <sub>oss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0, f=1.0MHz	-	3.0	-	-	3.7	-	pF
Q <sub>g(tot)</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =100mA	-	0.458	-	-	0.50	-	nC
Q <sub>gs</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =100mA	-	0.176	-	-	0.17	-	nC
Q <sub>gd</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =100mA	-	0.138	-	-	0.11	-	nC
t <sub>on</sub>	V <sub>DD</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =200mA	-	25	-	-	35	-	ns
t <sub>off</sub>	V <sub>DD</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =200mA	-	85	-	-	100	-	ns



www.centrasemi.com

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMRDM3575 consists of complementary N-Channel and P-Channel enhancement-mode silicon MOSFETs designed for high speed pulsed amplifier and driver applications. These MOSFETs offer low r<sub>DS(ON)</sub> and low threshold voltage.

**MARKING CODE: CT**

**FEATURES:**

- Power dissipation: 125mW
- Low package profile: 0.5mm (MAX)
- Low r<sub>DS(ON)</sub>
- Low threshold voltage
- Logic level compatible
- Small SOT-963 surface mount package

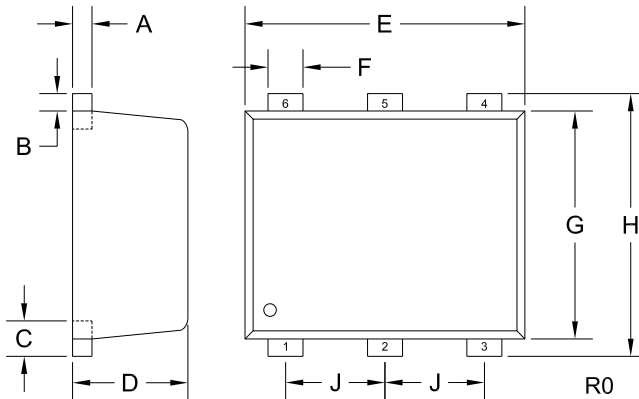
SYMBOL	N-CH (Q1)	P-CH (Q2)	UNITS
V <sub>DS</sub>		20	V
V <sub>GS</sub>		8.0	V
I <sub>D</sub>	160	140	mA
I <sub>D</sub>	200	180	mA
P <sub>D</sub>		125	mW
T <sub>J</sub> , T <sub>stg</sub>		-65 to +150	°C
θ <sub>JA</sub>		1000	°C/W

CMRDM3575

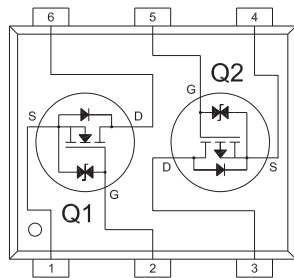
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**SOT-963 CASE - MECHANICAL OUTLINE**



**PIN CONFIGURATION**



**LEAD CODE:**

- 1) Source Q1
- 2) Gate Q1
- 3) Drain Q2
- 4) Source Q2
- 5) Gate Q2
- 6) Drain Q1

**MARKING CODE: CT**

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.002	0.006	0.050	0.150
B	0.002	0.006	0.050	0.150
C	0.005	0.007	0.125	0.175
D	0.016	0.020	0.400	0.500
E	0.037	0.041	0.950	1.050
F	0.004	0.008	0.100	0.200
G	0.030	0.033	0.750	0.850
H	0.037	0.041	0.950	1.050
J	0.014		0.350	

SOT-963 (REV: R0)

R3 (12-December 2012)